Highlights

Microwave induced transformation of defect in SiC and GaAs

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- The microwave irradiation increase interstitial defect concentration at near surface region
- Stress intensity the microwave induced defect transformation
- Microwave treatment decreases σ_n of vacancy related defects in SiC and GaAs single crystal
- The transient acoustoelectric spectroscopy used for determining properties of defects in SiC and GaAs.
- A microwave annealing of defects in SiC and GaAs was observed.